Abstract

Chromium-free Etching Solution for Si-substrates and SiGe-substrates, Method for Revealing Defects using the Etching Solution and Process for Treating Si-substrates and SiGe-substrates using the Etching Solution

The present invention relates to a novel etching solution suitable for characterizing defects on semiconductor surfaces, including silicon germanium surfaces, as well as a method for treating semiconductor surfaces with an etching solution as disclosed herein. This novel etching solution is chromium-free and enables a highly sufficient etch rate and highly satisfactory etch results.

Figure 3